

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S54	1418	(257/288).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/17 11:31
S55	1353	(438/197).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/17 11:31
S56	50124	gate near (dielectric oxide)	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 11:44
S57	779212	liner cap etch adj stop\$3	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 11:47
S58	583293	sin sion silicon adj nitride silicon adj oxy adj nitride	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 11:48
S59	2221	S57 near S58	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 11:49
S60	11877	sidewall near spacer	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 11:49
S61	82756	gate near electrode	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 11:49
S62	12539	S56 near5 S61	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 11:50
S63	272	S62 near5 S60	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 11:50
S64	0	S63 near5 S59	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 11:51
S65	0	S63 with S59	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 11:51
S66	65	S60 with S59	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 11:51
S67	42	S60 near5 S59	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 13:22

S68	31	S60 with ('sic' silicon adj carbide)	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 12:57
S69	17	S60 near5 ('sic' silicon adj carbide)	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 12:57
S70	12	S60 near3 ('sic' silicon adj carbide)	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 12:57
S71	3	("2001/0036713").URPN.	USPAT	OR	OFF	2005/11/17 13:01
S72	23	S66 not S67	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/17 13:22
S73	1	10/726380	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/17 13:48
S74	6	"6137126"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/09 10:41
S75	90	(conductive conducting conduct\$3 metal metalli\$3) near (sidewall side adj wall spacer) near2 gate with transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 15:16
S76	133	(conductive conducting conduct\$3 metal metalli\$3) near (sidewall side adj wall spacer) near2 gate with transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 15:09
S77	270	(conductive conducting conduct\$3 metal metalli\$3 polysilicon) near (sidewall side adj wall spacer) near2 gate with transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/22 16:08
S78	90	(conductive conducting conduct\$3 metal metalli\$3) near (sidewall side adj wall spacer) near2 gate with transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 16:48
S79	162542	(liner protect\$3) near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 16:49

S80	0	S78 with S79	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 16:49
S81	5	S78 and S79	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 16:50
S82	12	("6228695").URPN.	USPAT	OR	OFF	2005/11/30 17:01
S83	10	("4861730" "5063172" "5750427" "5824584" "5830794" "5858840" "6074914" "6117733" "6124609" "6133097").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/11/30 17:20
S84	1	"5897372".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/11/30 17:21
S85	20	("5897372").URPN.	USPAT	OR	OFF	2005/11/30 17:23
S86	2405	(conductive conducting conduct\$3 metal metal\$4) near3 (sidewall side adj wall side near3 wall) with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 16:31
S87	3545	(conductive conducting conduct\$3 metal metal\$4) near3 (sidewall side adj wall side near3 wall) with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 15:18
S88	2459	(conductive conducting conduct\$3 metal metal\$4) near2 (sidewall side adj wall side near3 wall) with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 15:18
S89	1832	(conductive conducting conduct\$3 metal metal\$4) near2 (sidewall side adj wall side near3 wall) near5 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 15:19
S90	869	(conductive conducting conduct\$3 metal metal\$4) near (sidewall side adj wall side near3 wall) near5 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 15:19
S91	70	(conductive conducting conduct\$3 metal metal\$4) near (sidewall side adj wall side near3 wall) near5 (gate with transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 16:28

S92	140910	nitride near5 (silicon adj nitride silicon adj oxynitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 16:29
S93	1171	liner near5 S92	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 16:30
S94	693	liner near2 S92	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 16:30
S95	503	liner near S92	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 16:30
S96	883	S92 near (liner protect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 16:30
S97	9	S96 near3 (sidewall side adj wall side near3 wall) with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 16:32
S98	32	S96 near3 (sidewall side adj wall side near3 wall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 16:32
S99	23	S98 not S97	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 16:32